

850 EVO Solid State Drives

250 GB	MZ-75E250B/AM	2 TB (2,000 GB)	MZ-75E2T0B/AM
500 GB	MZ-75E500B/AM, MZ-75E500E	4 TB (4,000 GB)	MZ-75E4T0B/AM
1 TB (1,000 GB)	MZ-75E1T0B/AM, MZ-75E1T0E		

SAMSUNG



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The advanced consumer SSD in a 2.5" form factor, powered by exclusive Samsung V-NAND technology.

- SATA 6Gb/s SSD for Client PCs
- Samsung Magician Software for SSD management
- 2.5 inch form factor
- Samsung Data Migration Software
- Samsung V-NAND 3bit MLC

Key features



V-NAND technology in the Samsung 850 EVO SSD

Samsung's unique V-NAND flash memory architecture is a breakthrough in overcoming the density, performance and endurance limitations of today's conventional planar NAND architecture. V-NAND is fabricated by stacking cell layers vertically, rather than decreasing the cells' dimensions to fit into increasingly smaller form factors. The result is higher density and better performance with a smaller footprint.



Optimized performance for everyday computing

Powered by Samsung's cutting-edge V-NAND technology, the 850 EVO delivers top-class sequential and random read and write performance to optimize everyday computing. With the improved performance that TurboWrite technology delivers, the 850 EVO provides a 10% better user experience than 840 EVO, as well as up to 1.9x/1.25x faster random write speeds for the 250 GB models. In fact, the 850 EVO delivers top-class sequential read (540 MB/s) and write (520 MB/s) performance in all capacities. And the 850 EVO delivers optimized random read and write performance on all QD, plus improved QD1 and QD2 random performance for Client PC usage.



Reinforcement of TurboWrite technology

Samsung was the first to introduce TurboWrite technology to sequential write performance. With TurboWrite Technology, write speeds have been significantly accelerated during data transfer by creating a high-performance write buffer in an SSD. If a consecutive write operation (i.e. no idle time) exceeds the size of a buffer, the transfer will exit TurboWrite and be processed at "After TurboWrite" speeds. But since the buffer size is more than sufficient for everyday computer use, users experience accelerated speeds for most workloads.



Guaranteed endurance and reliability for maximum use

The 850 EVO delivers guaranteed endurance and reliability by doubling the Terabytes Written (TBW) compared to the previous generation 840 EVO Series. The 850 EVO Series is backed by an industry-leading 5 year warranty or 75TBW (250 GB)/150TBW (500 GB, 1 TB)/300TBW (2 TB, 4 TB). With twice the endurance of a typical NAND flash SSD, the 850 EVO Series will keep working as long as you do.



Enhanced reliability with improved sustained performance

The 850 EVO Series boasts dependable performance up to 30% longer than the 840 EVO Series, with minimized performance degradation. You can use it every day, knowing it will perform at the highest levels for years.



Advanced data encryption

Self-Encrypting Drive (SED) security technology helps keep your data safe. An AES 256-bit hardware-based encryption engine secures your data without any of the performance degradation you might experience with software-based encryption. The 850 EVO is compliant with advanced security management solutions (TCG Opal and IEEE 1667), and you can erase or initialize data with the PSID crypto erase service.



Efficient power management for all PC applications

Since V-NAND uses half the power of 2D planar NAND, you save up to 50% more power during write operations than with the 840 EVO Series. And with a highly efficient 2mW Device Sleep feature and a controller optimized for V-NAND, you get longer battery life.

Samsung 850 EVO Solid State Drives



	MZ-75E250B/AM	MZ-75E500B/AM, MZ-75E500E	MZ-75E1T0B/AM, MZ-75E1T0E	MZ-75E2T0B/AM	MZ-75E4T0B/AM
Usage Application	Client PCs	Client PCs	Client PCs	Client PCs	Client PCs
Capacity ¹	250GB	500GB	1TB (1,000GB)	2TB (2,000GB)	4TB (4,000GB)
Dimensions (WxHxD)	100 x 69.85 x 6.8 (mm) / 3.94" x 2.75" x 0.27"	100 x 69.85 x 6.8 (mm) / 3.94" x 2.75" x 0.27"	100 x 69.85 x 6.8 (mm) / 3.94" x 2.75" x 0.27"	100 x 69.85 x 6.8 (mm) / 3.94" x 2.75" x 0.27"	100 x 69.85 x 6.8 (mm) / 3.94" x 2.75" x 0.27"
Interface	SATA 6Gb/s (Compatible with SATA 3Gb/s and SATA 1.5Gb/s)	SATA 6Gb/s (Compatible with SATA 3Gb/s and SATA 1.5Gb/s)	SATA 6Gb/s (Compatible with SATA 3Gb/s and SATA 1.5Gb/s)	SATA 6Gb/s (Compatible with SATA 3Gb/s and SATA 1.5Gb/s)	SATA 6Gb/s (Compatible with SATA 3Gb/s and SATA 1.5Gb/s)
Form Factor	2.5"	2.5"	2.5"	2.5"	2.5"
Controller	Samsung MGX Controller	Samsung MGX Controller	Samsung MGX Controller	Samsung MHX Controller	Samsung MHX Controller
NAND Flash Memory	Samsung V-NAND 3bit MLC	Samsung V-NAND 3bit MLC	Samsung V-NAND 3bit MLC	Samsung V-NAND 3bit MLC	Samsung V-NAND 3bit MLC
DRAM Cache Memory	512MB LPDDR3	512MB LPDDR3	1GB LPDDR3	2GB LPDDR3	4GB LPDDR3
Performance ²	Sequential Read (Max.):	540 MB/s	540 MB/s	540 MB/s	540 MB/s
	Sequential Write ³ (Max.):	520 MB/s	520 MB/s	520 MB/s	520 MB/s
	4KB Random Read (QD1)(Max.):	10,000 IOPS	10,000 IOPS	10,000 IOPS	10,000 IOPS
	4KB Random Write (QD1)(Max.):	40,000 IOPS	40,000 IOPS	40,000 IOPS	40,000 IOPS
	4KB Random Read (QD32)(Max.):	97,000 IOPS	98,000 IOPS	98,000 IOPS	98,000 IOPS
	4KB Random Write (QD32)(Max.):	88,000 IOPS	90,000 IOPS	90,000 IOPS	90,000 IOPS
Data Security	AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)	AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)	AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)	AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)	AES 256-bit Full Disk Encryption, TCG/Opal V2.0, Encrypted Drive (IEEE1667)
Weight (Max.)	55g	55g	55g	55g	55g
Reliability (MTBF)	1.5 Million Hours	1.5 Million Hours	1.5 Million Hours	1.5 Million Hours	1.5 Million Hours
TBW (Terabytes Written)	75TBW	150TBW	150TBW	300TBW	300TBW
Power Consumption ⁴	Active Read/Write (Average/Max.):	3.1W / 3.6W	3.1W / 3.6W	3.1W / 3.6W	3.1W / 3.6W
	Idle (Max.):	70mW	70mW	70mW	70mW
	Device Sleep (Typ.):	2mW	2mW	4mW	5mW
Supporting Features	TRIM (Required OS Support), Garbage Collection, S.M.A.R.T	TRIM (Required OS Support), Garbage Collection, S.M.A.R.T	TRIM (Required OS Support), Garbage Collection, S.M.A.R.T	TRIM (Required OS Support), Garbage Collection, S.M.A.R.T	TRIM (Required OS Support), Garbage Collection, S.M.A.R.T
Temperature	Operating:	0°C to 70°C	0°C to 70°C	0°C to 70°C	0°C to 70°C
	Non-Operating:	-40°C to 85°C	-40°C to 85°C	-40°C to 85°C	-40°C to 85°C
Humidity	5% to 95%, Non-Condensing	5% to 95%, Non-Condensing	5% to 95%, Non-Condensing	5% to 95%, Non-Condensing	5% to 95%, Non-Condensing
Vibration (Non-Operating)	20–2000Hz, 20G	20–2000Hz, 20G	20–2000Hz, 20G	20–2000Hz, 20G	20–2000Hz, 20G
Shock (Non-Operating)	1500G, Duration 0.5m Sec, 3 Axis	1500G, Duration 0.5m Sec, 3 Axis	1500G, Duration 0.5m Sec, 3 Axis	1500G, Duration 0.5m Sec, 3 Axis	1500G, Duration 0.5m Sec, 3 Axis
Warranty	5 Years Limited	5 Years Limited	5 Years Limited	5 Years Limited	5 Years Limited

¹1GB = 1,000,000,000 bytes. Actual usable capacity may be less (due to formatting, partitioning, operating system, applications or otherwise).

²Sequential performance measurements based on CrystalDiskMark v.3.0.1.1. Random performance measurements based on Iometer 1.1.0. Performance may vary based on SSD's firmware version, system hardware and configuration. Test system configuration: Intel Core i7-4790K @ 4.0GHz, DDR3 1600MHz 8GB, OS: Windows 7 Ultimate x64 SP1, IRST 13.0.3.1001, Chipset: Intel® Z97PR0.

³Sequential Write performance measurements based on TurboWrite technology. The sequential write performances after TurboWrite region are 300MB/s (250GB) and 500MB/s (500GB/1TB).

⁴Power consumption measured with Iometer 1.1.0 with Intel i7-4770K, DDR3 8GB, Intel® DH87RL, OS: Windows 7 Ultimate x64 SP1.



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